TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# ТРСР8007-Н

Switching Regulator Applications Motor Drive Applications DC-DC Converter Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 2.7 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS(ON)} = 40 \text{ m}\Omega \text{ (typ.)}$ 

- High forward transfer admittance: |Y<sub>fs</sub>| = 16 S (typ.)
- Low leakage current: I<sub>DSS</sub> = 10 μA (max) (V<sub>DS</sub> = 60 V)
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.1 mA)

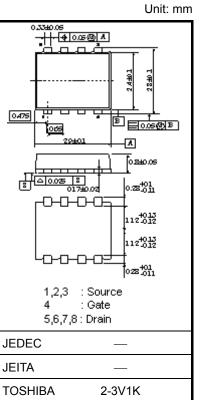
#### Absolute Maximum Ratings (Ta = 25°C)

| Characte                    | eristic                      | Symbol           | Rating     | Unit |
|-----------------------------|------------------------------|------------------|------------|------|
| Drain-source voltage        |                              | V <sub>DSS</sub> | 60         | V    |
| Drain-gate voltage (R       | t <sub>GS</sub> = 20 kΩ)     | V <sub>DGR</sub> | 60         | V    |
| Gate-source voltage         |                              | V <sub>GSS</sub> | ±20        | V    |
| Drain current               | DC (Note 1)                  | ۱ <sub>D</sub>   | 5          | А    |
|                             | Pulsed (Note 1)              | I <sub>DP</sub>  | 20         | А    |
| Drain power dissipati       | on (t = 5 s)<br>(Note 2a)    | PD               | 1.68       | W    |
| Drain power dissipati       | on (t = 5 s)<br>(Note 2b)    | PD               | 0.84       | w    |
| Single-pulse avalance       | ne energy<br>(Note 3)        | E <sub>AS</sub>  | 9          | mJ   |
| Avalanche current           |                              | I <sub>AR</sub>  | 5          | А    |
| Repetitive avalanche<br>(To | energy<br>c = 25°C) (Note 4) | E <sub>AR</sub>  | 0.05       | mJ   |
| Channel temperature         |                              | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature         | range                        | T <sub>stg</sub> | -55 to 150 | °C   |

Note: For Notes 1 to 5, refer to the next page.

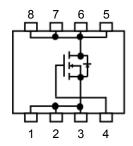
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

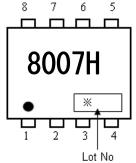


Weight: 0.017g (typ.)

#### **Circuit Configuration**



#### Marking (Note 5)

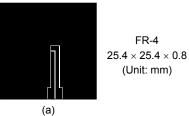


### **Thermal Characteristics**

| Characteristic                                               | Symbol                 | Max   | Unit |
|--------------------------------------------------------------|------------------------|-------|------|
| Thermal resistance, channel to ambient $(t = 5 s)$ (Note 2a) | R <sub>th (ch-a)</sub> | 74.4  | °C/W |
| Thermal resistance, channel to ambient $(t = 5 s)$ (Note 2b) | R <sub>th (ch-a)</sub> | 148.8 | °C/W |

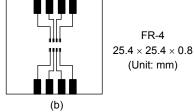
Note 1: Ensure that the channel temperature does not exceed 150  $^{\circ}\text{C}.$ 

Note 2: (a) Device mounted on a glass-epoxy board (a)





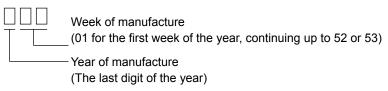
(b) Device mounted on a glass-epoxy board (b)



Note 3: V\_DD = 24 V, T\_{ch} = 25 ^{\circ}C (initial), L = 500  $\mu$ H, R\_G = 1  $\Omega$ , I\_AR = 5 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)

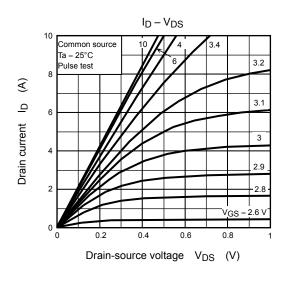


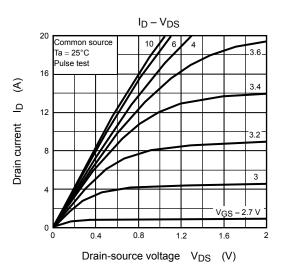
Electrical Characteristics (Ta = 25°C)

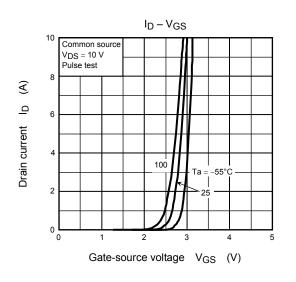
| Ch                           | Characteristic                 |                      | Test Condition                                                                   | Min         | Тур. | Max  | Unit |
|------------------------------|--------------------------------|----------------------|----------------------------------------------------------------------------------|-------------|------|------|------|
| Gate leakage cur             | rrent                          | I <sub>GSS</sub>     | $V_{GS}=\pm 20~V,~V_{DS}=0~V$                                                    | —           |      | ±100 | nA   |
| Drain cutoff curre           | ent                            | I <sub>DSS</sub>     | $V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$                            | _           |      | 10   | μA   |
| Drain source bro             | Prain-source breakdown voltage |                      | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$                                      | 60          |      |      | V    |
| Drain-source brea            | akuown vollage                 | V (BR) DSX           | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$                                    | 45 <u> </u> |      |      |      |
| Gate threshold vo            | oltage                         | V <sub>th</sub>      | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$                          | 1.3         | _    | 2.3  | V    |
| Drain-source ON-resistance   |                                | Bag (out)            | $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$                          | _           | 47   | 64   | m0   |
| Drain-source ON              | resistance                     | R <sub>DS</sub> (ON) | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$                           | _           | 40   | 57   | mΩ   |
| Forward transfer             | admittance                     | Y <sub>fs</sub>      | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$                           | 8           | 16   | _    | S    |
| Input capacitance            | 9                              | C <sub>iss</sub>     |                                                                                  | _           | 640  | 900  |      |
| Reverse transfer             | capacitance                    | C <sub>rss</sub>     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                         | _           | 25   | 40   | pF   |
| Output capacitance           |                                | C <sub>oss</sub>     |                                                                                  |             | 90   |      |      |
| Gate resistance              |                                | rg                   | $V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$ | _           | 3.2  | 4.6  | Ω    |
| Switching time               | Rise time                      | tr                   | $V_{GS} \stackrel{10}{}_{0} V \qquad I_{D} = 2.5 A$                              | _           | 2.4  | _    | - ns |
|                              | Turn-on time                   | t <sub>on</sub>      |                                                                                  | _           | 7.8  | _    |      |
|                              | Fall time                      | t <sub>f</sub>       |                                                                                  | _           | 2.4  | _    |      |
|                              | Turn-off time                  | t <sub>off</sub>     | $V_{DD}\approx 30~V$ Duty $\leq$ 1%, $t_W=10~\mu s$                              | _           | 18   | _    |      |
| Total gate charge            | Total gate charge              |                      | $V_{DD}\approx 48~V,~V_{GS}=10~V,~I_{D}=5~A$                                     |             | 11   |      |      |
| (gate-source plus            | gate-drain)                    | Qg                   | $V_{DD}\approx 48~V,~V_{GS}=5~V,~I_{D}=5~A$                                      | = 5 A — 5   |      |      |      |
| Gate-source charge 1         |                                | Q <sub>gs1</sub>     |                                                                                  |             | 2.3  |      | nC   |
| Gate-drain ("Miller") charge |                                | Q <sub>gd</sub>      | $V_{DD} \approx 48$ V, $V_{GS} = 10$ V, $I_D = 5$ A                              |             | 1.7  |      |      |
| Gate switch char             | ge                             | Q <sub>SW</sub>      | 1                                                                                |             | 2.7  |      |      |

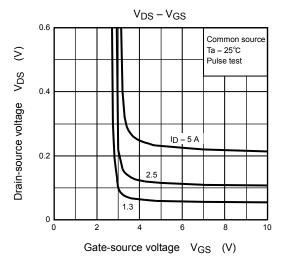
### Source-Drain Ratings and Characteristics (Ta = 25°C)

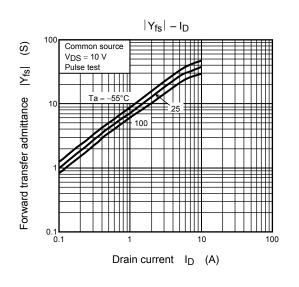
| Characteristic          |       | Symbol   | Test Condition   | Min                                          | Тур. | Max | Unit |   |
|-------------------------|-------|----------|------------------|----------------------------------------------|------|-----|------|---|
| Peak forward current    | Pulse | (Note 1) | I <sub>FP</sub>  | —                                            | _    |     | 20   | А |
| Forward voltage (diode) |       |          | V <sub>DSF</sub> | $I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V}$ |      |     | -1.2 | V |

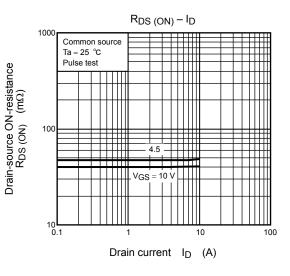


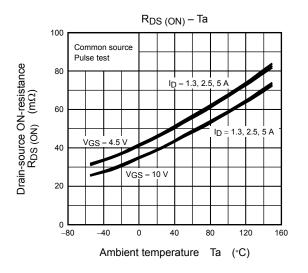


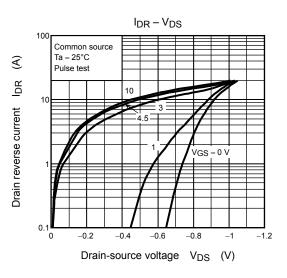


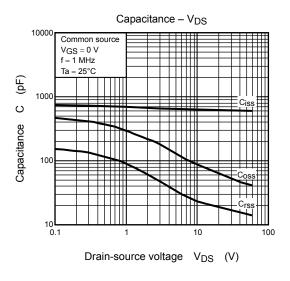


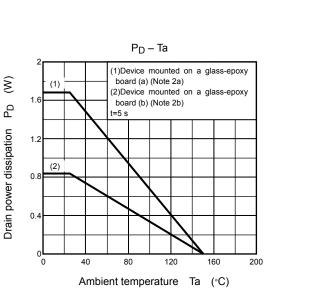


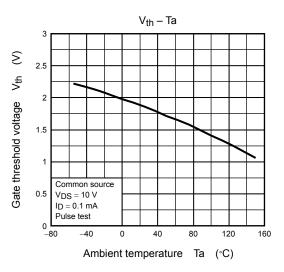


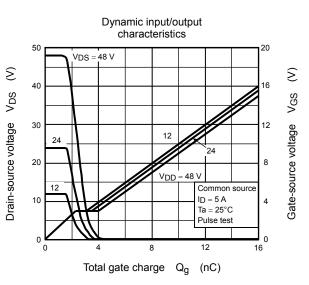


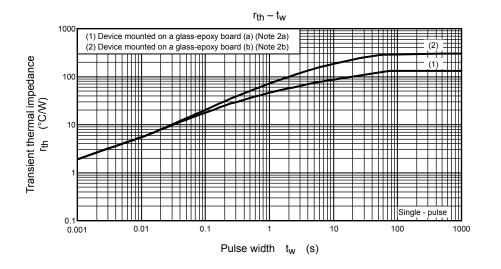


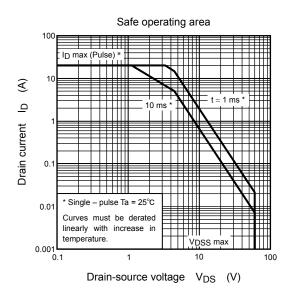












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